

HD Communications Corp. Solid State Broadband High Power RF Amplifier

Ronkonkoma, NY USA

HD17070

Home of RFamplifiers.com

1 – 500 MHz / 10 Watt

Designed for broadband high power linear applications, this amplifier utilizes Silicon RF Power MOSFET devices that provide high gain, wide dynamic range and good linearity. Exceptional performance, long term reliability and high efficiency are achieved by employing advanced broadband RF matching networks and combining techniques, EMI/RFI filters, custom-machined housings and qualified components. Each unit undergoes extensive burn-in prior to final test and inspection.

ELECTRICAL SPECIFICATIONS @ 28 VDC, 25°C

Characteristics	Rating	Limit
Frequency Response	1 – 500 MHz	Min
Power Output CW	10 Watts	Min
Power Output @ 1 dB comp.	8 Watts	Min
Small Signal Gain	40 dB	Min
Small Signal Gain Flatness	±1.5 dB	Max
Third Order Intercept Point	+49 dBm	Typ
Input Overdrive	+10 dBm	Max
Input/Output VSWR @ 50 ohm	2:1	Max
Harmonics @ 1 dB compression	-25 dBc	Typ
Noise Figure	10 dB	Max
Input Signal Format	AM/PM/FM/PM/Pulse	Typ
Spurious Signals	-60 dBc	Max
Operating Voltage	24 - 30 VDC	Nom
Current Consumption	2.5 Amp	Max

ENVIRONMENTAL CHARACTERISTICS

Operating Temperature: 0°C to +50°C
Non-operating Temperature: -40°C to +85°C
Humidity: 95% relative without condensation
Altitude: 10,000 feet
Shock and Vibration: Normal truck transport

CIRCUIT PROTECTIONS

Infinite Load VSWR open or short
RF Input Overdrive

MECHANICAL SPECIFICATIONS

Dimensions	6"x3"x1.1"	Max
Weight	1.0 lb.	Max
RF Connectors	SMA female	
Cooling	External Heatsink	

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